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### Understanding [Embedded - Microprocessors](#)

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

### Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Product Status	Obsolete
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (1), 10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	783-BFBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8540pxaqfb">https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8540pxaqfb</a>

- 256 Kbyte L2 cache/SRAM
  - Can be configured as follows
    - Full cache mode (256-Kbyte cache).
    - Full memory-mapped SRAM mode (256-Kbyte SRAM mapped as a single 256-Kbyte block or two 128-Kbyte blocks)
    - Half SRAM and half cache mode (128-Kbyte cache and 128-Kbyte memory-mapped SRAM)
  - Full ECC support on 64-bit boundary in both cache and SRAM modes
  - Cache mode supports instruction caching, data caching, or both
  - External masters can force data to be allocated into the cache through programmed memory ranges or special transaction types (stashing)
  - Eight-way set-associative cache organization (1024 sets of 32-byte cache lines)
  - Supports locking the entire cache or selected lines. Individual line locks are set and cleared through Book E instructions or by externally mastered transactions
  - Global locking and flash clearing done through writes to L2 configuration registers
  - Instruction and data locks can be flash cleared separately
  - Read and write buffering for internal bus accesses
  - SRAM features include the following:
    - I/O devices access SRAM regions by marking transactions as snoopable (global)
    - Regions can reside at any aligned location in the memory map
    - Byte accessible ECC is protected using read-modify-write transactions accesses for smaller than cache-line accesses.
- Address translation and mapping unit (ATMU)
  - Eight local access windows define mapping within local 32-bit address space
  - Inbound and outbound ATMUs map to larger external address spaces
    - Three inbound windows plus a configuration window on PCI/PCI-X
    - Four inbound windows plus a default and configuration window on RapidIO
    - Four outbound windows plus default translation for PCI
    - Eight outbound windows plus default translation for RapidIO
- DDR memory controller
  - Programmable timing supporting DDR-1 SDRAM
  - 64-bit data interface, up to 333-MHz data rate
  - Four banks of memory supported, each up to 1 Gbyte
  - DRAM chip configurations from 64 Mbits to 1 Gbit with x8/x16 data ports
  - Full ECC support
  - Page mode support (up to 16 simultaneous open pages)
  - Contiguous or discontinuous memory mapping

- Read-modify-write support for RapidIO atomic increment, decrement, set, and clear transactions
- Sleep mode support for self refresh SDRAM
- Supports auto refreshing
- On-the-fly power management using CKE signal
- Registered DIMM support
- Fast memory access via JTAG port
- 2.5-V SSTL2 compatible I/O
- RapidIO interface unit
  - 8-bit RapidIO I/O and messaging protocols
  - Source-synchronous double data rate (DDR) interfaces
  - Supports small type systems (small domain, 8-bit device ID)
  - Supports four priority levels (ordering within a level)
  - Reordering across priority levels
  - Maximum data payload of 256 bytes per packet
  - Packet pacing support at the physical layer
  - CRC protection for packets
  - Supports atomic operations increment, decrement, set, and clear
  - LVDS signaling
- RapidIO-compliant message unit
  - One inbound data message structure (inbox)
  - One outbound data message structure (outbox)
  - Supports chaining and direct modes in the outbox
  - Support of up to 16 packets per message
  - Support of up to 256 bytes per packet and up to 4 Kbytes of data per message
  - Supports one inbound doorbell message structure
- Programmable interrupt controller (PIC)
  - Programming model is compliant with the OpenPIC architecture
  - Supports 16 programmable interrupt and processor task priority levels
  - Supports 12 discrete external interrupts
  - Supports 4 message interrupts with 32-bit messages
  - Supports connection of an external interrupt controller such as the 8259 programmable interrupt controller
  - Four global high resolution timers/counters that can generate interrupts
  - Supports 22 other internal interrupt sources
  - Supports fully nested interrupt delivery
  - Interrupts can be routed to external pin for external processing

## 2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

### 2.1.1 Absolute Maximum Ratings

Table 1 provides the absolute maximum ratings.

**Table 1. Absolute Maximum Ratings**<sup>1</sup>

Characteristic		Symbol	Max Value	Unit	Notes
Core supply voltage For devices rated at 667 and 833 MHz For devices rated at 1 GHz		$V_{DD}$	-0.3 to 1.32 -0.3 to 1.43	V	
PLL supply voltage For devices rated at 667 and 833 MHz For devices rated at 1 GHz		$AV_{DD}$	-0.3 to 1.32 -0.3 to 1.43	V	
DDR DRAM I/O voltage		$GV_{DD}$	-0.3 to 3.63	V	
Three-speed Ethernet I/O voltage		$LV_{DD}$	-0.3 to 3.63 -0.3 to 2.75	V	
PCI/PCI-X, local bus, RapidIO, 10/100 Ethernet, MII management, DUART, system control and power management, I <sup>2</sup> C, and JTAG I/O voltage		$OV_{DD}$	-0.3 to 3.63	V	3
Input voltage	DDR DRAM signals	$MV_{IN}$	-0.3 to ( $GV_{DD} + 0.3$ )	V	2, 5
	DDR DRAM reference	$MV_{REF}$	-0.3 to ( $GV_{DD} + 0.3$ )	V	2, 5
	Three-speed Ethernet signals	$LV_{IN}$	-0.3 to ( $LV_{DD} + 0.3$ )	V	4, 5
	Local bus, RapidIO, 10/100 Ethernet, DUART, SYSCLK, system control and power management, I <sup>2</sup> C, and JTAG signals	$OV_{IN}$	-0.3 to ( $OV_{DD} + 0.3$ )	V	5
	PCI/PCI-X	$OV_{IN}$	-0.3 to ( $OV_{DD} + 0.3$ )	V	6
Storage temperature range		$T_{STG}$	-55 to 150	•C	

**Notes:**

- Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause permanent damage to the device.
- Caution:**  $MV_{IN}$  must not exceed  $GV_{DD}$  by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- Caution:**  $OV_{IN}$  must not exceed  $OV_{DD}$  by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- Caution:**  $LV_{IN}$  must not exceed  $LV_{DD}$  by more than 0.3 V. This limit may be exceeded for a maximum of 20 ms during power-on reset and power-down sequences.
- (M,L,O) $V_{IN}$  and  $MV_{REF}$  may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.
- $OV_{IN}$  on the PCI interface may overshoot/undershoot according to the PCI Electrical Specification for 3.3-V operation, as shown in Figure 3.

**Table 11. RESET Initialization Timing Specifications (continued)**

Parameter/Condition	Min	Max	Unit	Notes
Maximum valid-to-high impedance time for actively driven POR configs with respect to negation of HRESET	—	5	SYSCLKs	1

**Notes:**

1. SYSCLK is identical to the PCI\_CLK signal and is the primary clock input for the MPC8540. See the MPC8540 Integrated Processor Preliminary Reference Manual for more details.

Table 12 provides the PLL and DLL lock times.

**Table 12. PLL and DLL Lock Times**

Parameter/Condition	Min	Max	Unit	Notes
PLL lock times	—	100	μs	
DLL lock times	7680	122,880	CCB Clocks	1, 2

**Notes:**

1. DLL lock times are a function of the ratio between the output clock and the platform (or CCB) clock. A 2:1 ratio results in the minimum and an 8:1 ratio results in the maximum.
2. The CCB clock is determined by the SYSCLK × platform PLL ratio.

## 6 DDR SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface of the MPC8540.

### 6.1 DDR SDRAM DC Electrical Characteristics

Table 13 provides the recommended operating conditions for the DDR SDRAM component(s) of the MPC8540.

**Table 13. DDR SDRAM DC Electrical Characteristics**

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	$GV_{DD}$	2.375	2.625	V	1
I/O reference voltage	$MV_{REF}$	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	$V_{TT}$	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	$V_{IH}$	$MV_{REF} + 0.18$	$GV_{DD} + 0.3$	V	4
Input low voltage	$V_{IL}$	-0.3	$MV_{REF} - 0.18$	V	4
Output leakage current	$I_{OZ}$	-10	10	μA	5
Output high current ( $V_{OUT} = 1.95$ V)	$I_{OH}$	-15.2	—	mA	
Output low current ( $V_{OUT} = 0.35$ V)	$I_{OL}$	15.2	—	mA	

### 8.2.3.2 TBI Receive AC Timing Specifications

Table 28 provides the TBI receive AC timing specifications.

**Table 28. TBI Receive AC Timing Specifications**

At recommended operating conditions with  $LV_{DD}$  of  $3.3\text{ V} \pm 5\%$ , or  $LV_{DD}=2.5\text{ V} \pm 5\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit
RX_CLK clock period	$t_{TRX}$		16.0		ns
RX_CLK skew	$t_{SKTRX}$	7.5	—	8.5	ns
RX_CLK duty cycle	$t_{TRXH}/t_{TRX}$	40	—	60	%
RCG[9:0] setup time to rising RX_CLK	$t_{TRDVKH}$	2.5	—	—	ns
RCG[9:0] hold time to rising RX_CLK	$t_{TRDXKH}$	1.5	—	—	ns
RX_CLK clock rise time and fall time	$t_{TRXR}, t_{TRXF}$ <sup>2,3</sup>	0.7	—	2.4	ns

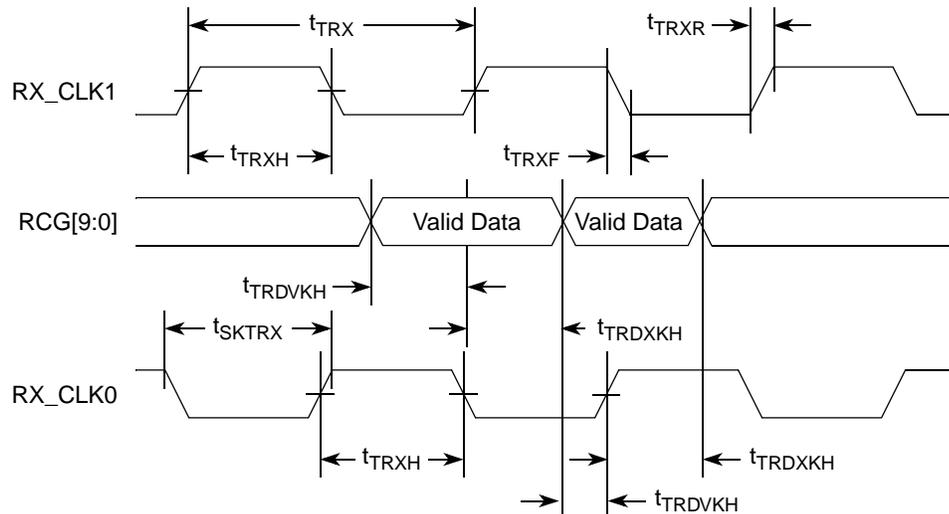
**Note:**

1. The symbols used for timing specifications herein follow the pattern of  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})}$  (reference)(state) for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{TRDVKH}$  symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the  $t_{TRX}$  clock reference (K) going to the high (H) state or setup time. Also,  $t_{TRDXKH}$  symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the  $t_{TRX}$  clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of  $t_{TRX}$  represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).

2. Signal timings are measured at 0.7 V and 1.9 V voltage levels.

3. Guaranteed by design.

Figure 13 shows the TBI receive AC timing diagram.



**Figure 13. TBI Receive AC Timing Diagram**

## 8.4.2 MII Management AC Electrical Specifications

Table 34 provides the MII management AC timing specifications.

**Table 34. MII Management AC Timing Specifications**

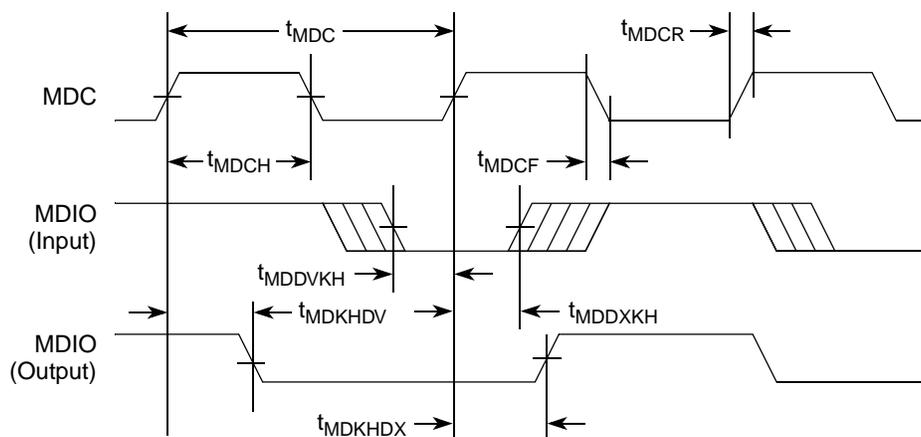
At recommended operating conditions with  $OV_{DD}$  is  $3.3\text{ V} \pm 5\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
MDC frequency	$f_{MDC}$	0.893	—	10.4	MHz	2, 4
MDC period	$t_{MDC}$	96	—	1120	ns	
MDC clock pulse width high	$t_{MDCH}$	32	—	—	ns	
MDC to MDIO valid	$t_{MDKHDV}$			$2 \cdot [1/(f_{ccb\_clk}/8)]$	ns	3
MDC to MDIO delay	$t_{MDKHDX}$	10	—	$2 \cdot [1/(f_{ccb\_clk}/8)]$	ns	3
MDIO to MDC setup time	$t_{MDDVKH}$	5	—	—	ns	
MDIO to MDC hold time	$t_{MDDXKH}$	0	—	—	ns	
MDC rise time	$t_{MDCR}$	—	—	10	ns	4
MDC fall time	$t_{MDHF}$	—	—	10	ns	4

**Notes:**

- The symbols used for timing specifications herein follow the pattern of  $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)}$  (reference)(state) for inputs and  $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$  for outputs. For example,  $t_{MDKHDX}$  symbolizes management data timing (MD) for the time  $t_{MDC}$  from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also,  $t_{MDDVKH}$  symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the  $t_{MDC}$  clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- This parameter is dependent on the CCB clock speed (that is, for a CCB clock of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a CCB clock of 333 MHz, the maximum frequency is 10.4 MHz and the minimum frequency is 1.5 MHz).
- This parameter is dependent on the CCB clock speed (that is, for a CCB clock of 267 MHz, the delay is 60 ns and for a CCB clock of 333 MHz, the delay is 48 ns).
- Guaranteed by design.

Figure 17 shows the MII management AC timing diagram.



**Figure 17. MII Management Interface Timing Diagram**

Figure 25 provides the AC test load for TDO and the boundary-scan outputs of the MPC8540.

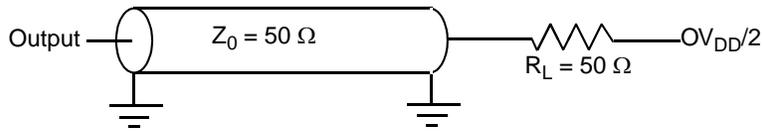


Figure 25. AC Test Load for the JTAG Interface

Figure 26 provides the JTAG clock input timing diagram.

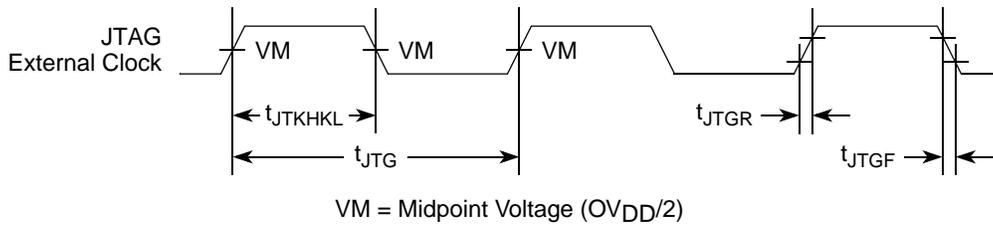


Figure 26. JTAG Clock Input Timing Diagram

Figure 27 provides the  $\overline{TRST}$  timing diagram.

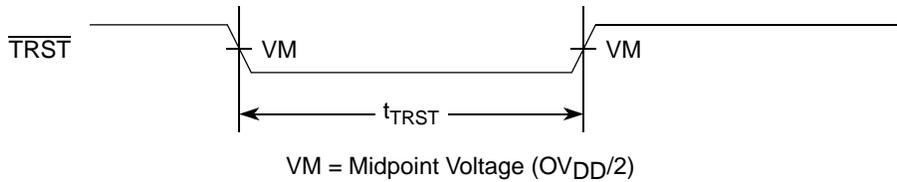


Figure 27.  $\overline{TRST}$  Timing Diagram

Figure 28 provides the boundary-scan timing diagram.

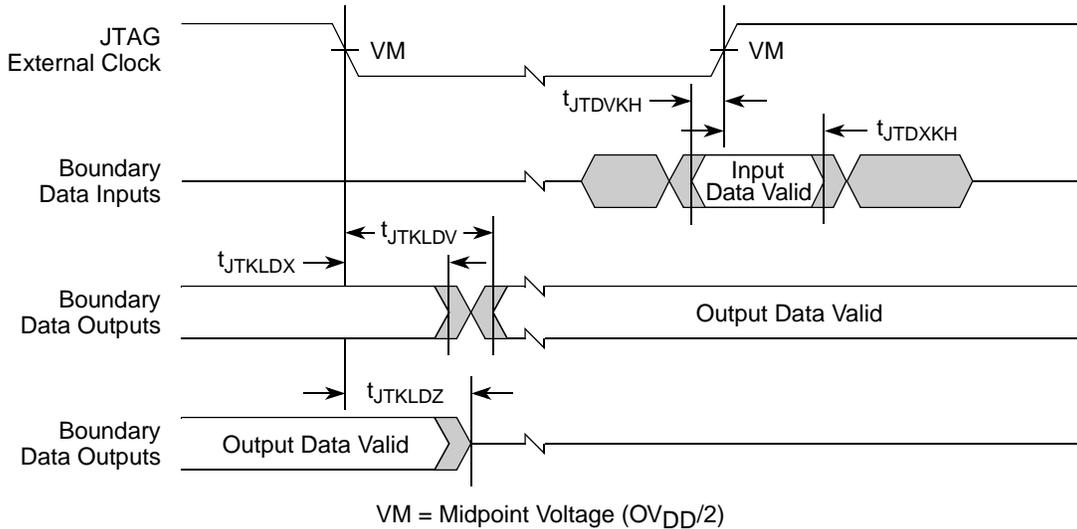


Figure 28. Boundary-Scan Timing Diagram

Figure 18 provides the AC test load for PCI and PCI-X.

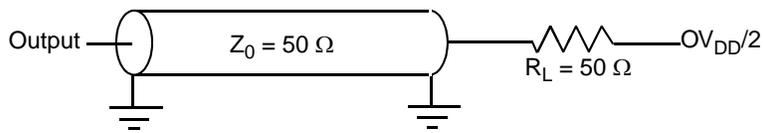


Figure 32. PCI/PCI-X AC Test Load

Figure 33 shows the PCI/PCI-X input AC timing conditions.

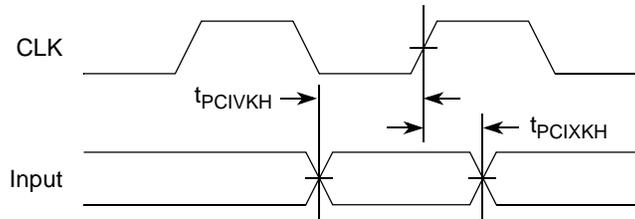


Figure 33. PCI-PCI-X Input AC Timing Measurement Conditions

Figure 34 shows the PCI/PCI-X output AC timing conditions.

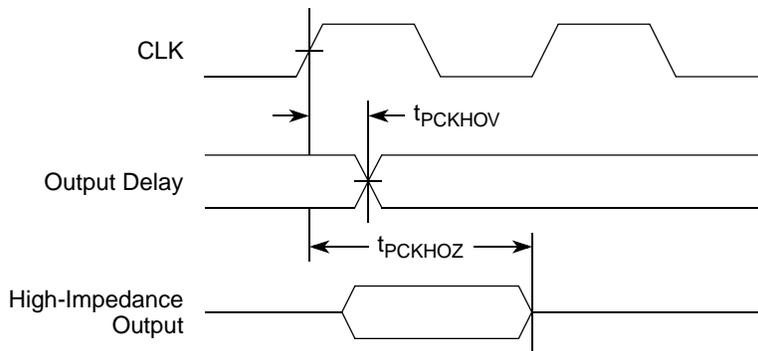


Figure 34. PCI-PCI-X Output AC Timing Measurement Condition

Table 43 provides the PCI-X AC timing specifications at 66 MHz.

Table 43. PCI-X AC Timing Specifications at 66 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	$t_{PCKHOV}$	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	$t_{PCKHOX}$	0.7	—	ns	1, 10
SYSCLK to output high impedance	$t_{PCKHOZ}$	—	7	ns	1, 4, 8, 11
Input setup time to SYSCLK	$t_{PCIVKH}$	1.7	—	ns	3, 5
Input hold time from SYSCLK	$t_{PCIXKH}$	0.5	—	ns	10
$\overline{REQ64}$ to $\overline{HRESET}$ setup time	$t_{PCRVRH}$	10	—	clocks	11
$\overline{HRESET}$ to $\overline{REQ64}$ hold time	$t_{PCRHRX}$	0	50	ns	11
$\overline{HRESET}$ high to first $\overline{FRAME}$ assertion	$t_{PCRHFV}$	10	—	clocks	9, 11

**Table 45. RapidIO 8/16 LP-LVDS Driver DC Electrical Characteristics (continued)**At recommended operating conditions with  $OV_{DD}$  of  $3.3\text{ V} \pm 5\%$ .

Characteristic	Symbol	Min	Max	Unit	Notes
Common mode offset voltage	$\Delta V_{OSCM}$	—	50	mV	1, 6
Differential termination	$R_{TERM}$	90	220	W	
Short circuit current (either output)	$ I_{SS} $	—	24	mA	7
Bridged short circuit current	$ I_{SB} $	—	12	mA	8

**Notes:**

1. Bridged 100- $\Omega$  load.
2. See [Figure 35\(a\)](#).
3. Differential offset voltage =  $|V_{OHD} + V_{OLD}|$ . See [Figure 35\(b\)](#).
4.  $V_{OHCM} = (V_{OA} + V_{OB})/2$  when measuring  $V_{OHD}$ .
5.  $V_{OLCM} = (V_{OA} + V_{OB})/2$  when measuring  $V_{OLD}$ .
6. Common mode offset  $\Delta V_{OSCM} = |V_{OHCM} - V_{OLCM}|$ . See [Figure 35\(c\)](#).
7. Outputs shorted to  $V_{DD}$  or GND.
8. Outputs shorted together.

**Table 46. RapidIO 8/16 LP-LVDS Receiver DC Electrical Characteristics**

Characteristic	Symbol	Min	Max	Unit	Notes
Voltage at either input	$V_I$	0	2.4	V	
Differential input high voltage	$V_{IHD}$	100	600	mV	1
Differential input low voltage	$V_{ILD}$	-600	-100	mV	1
Common mode input range (referenced to receiver ground)	$V_{ICM}$	0.050	2.350	V	2
Input differential resistance	$R_{IN}$	90	110	W	

**Notes:**

1. Over the common mode range.
2. Limited by  $V_I$ . See [Figure 42](#).

enough that increasing the length of the sequence does not cause the resulting eye pattern to change from one that complies with the RapidIO receive mask to one that does not comply with the mask. The data carried by any given data signal in the interface may not be correlated with the data carried by any other data signal in the interface. The zero-crossings of the clock associated with a data signal shall be used as the timing reference for aligning the multiple recordings of the data signal when the recordings are overlaid.

While the method used to make the recordings and overlay them to form the eye pattern is not specified, the method used shall be demonstrably equivalent to the following method. The signal under test is repeatedly recorded with a digital oscilloscope in infinite persistence mode. Each recording is triggered by a zero-crossing of the clock associated with the data signal under test. Roughly half of the recordings are triggered by positive-going clock zero-crossings and roughly half are triggered by negative-going clock zero-crossings. Each recording is at least 1.9 UI in length (to ensure that at least one complete eye is formed) and begins 0.5 UI before the trigger point (0.5 UI before the associated clock zero-crossing). Depending on the length of the individual recordings used to generate the eye pattern, one or more complete eyes will be formed. Regardless of the number of eyes, the eye whose center is immediately to the right of the trigger point is the eye used for compliance testing.

An example of an eye pattern generated using the above method with recordings 3 UI in length is shown in Figure 41. In this example, there is no skew between the signal under test and the associated clock used to trigger the recordings. If skew was present, the eye pattern would be shifted to the left or right relative to the oscilloscope trigger point.

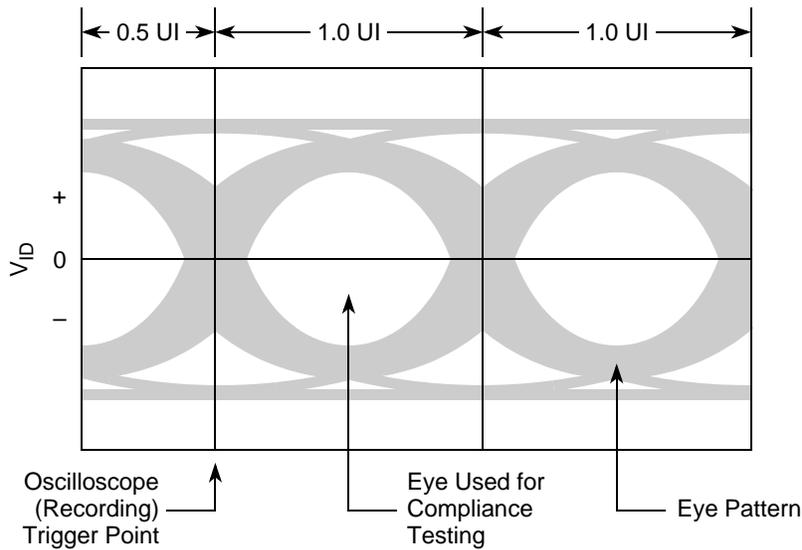


Figure 41. Example Receiver Input Eye Pattern

## 14 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions.

### 14.1 Package Parameters for the MPC8540 FC-PBGA

The package parameters are as provided in the following list. The package type is 29 mm × 29 mm, 783 flip chip plastic ball grid array (FC-PBGA).

Die size	12.2 mm × 9.5 mm
Package outline	29 mm × 29 mm
Interconnects	783
Pitch	1 mm
Minimum module height	3.07 mm
Maximum module height	3.75 mm
Solder Balls	62 Sn/36 Pb/2 Ag
Ball diameter (typical)	0.5 mm

## 14.2 Mechanical Dimensions of the MPC8540 FC-PBGA

Figure 44 the mechanical dimensions and bottom surface nomenclature of the MPC8540, 783 FC-PBGA package.

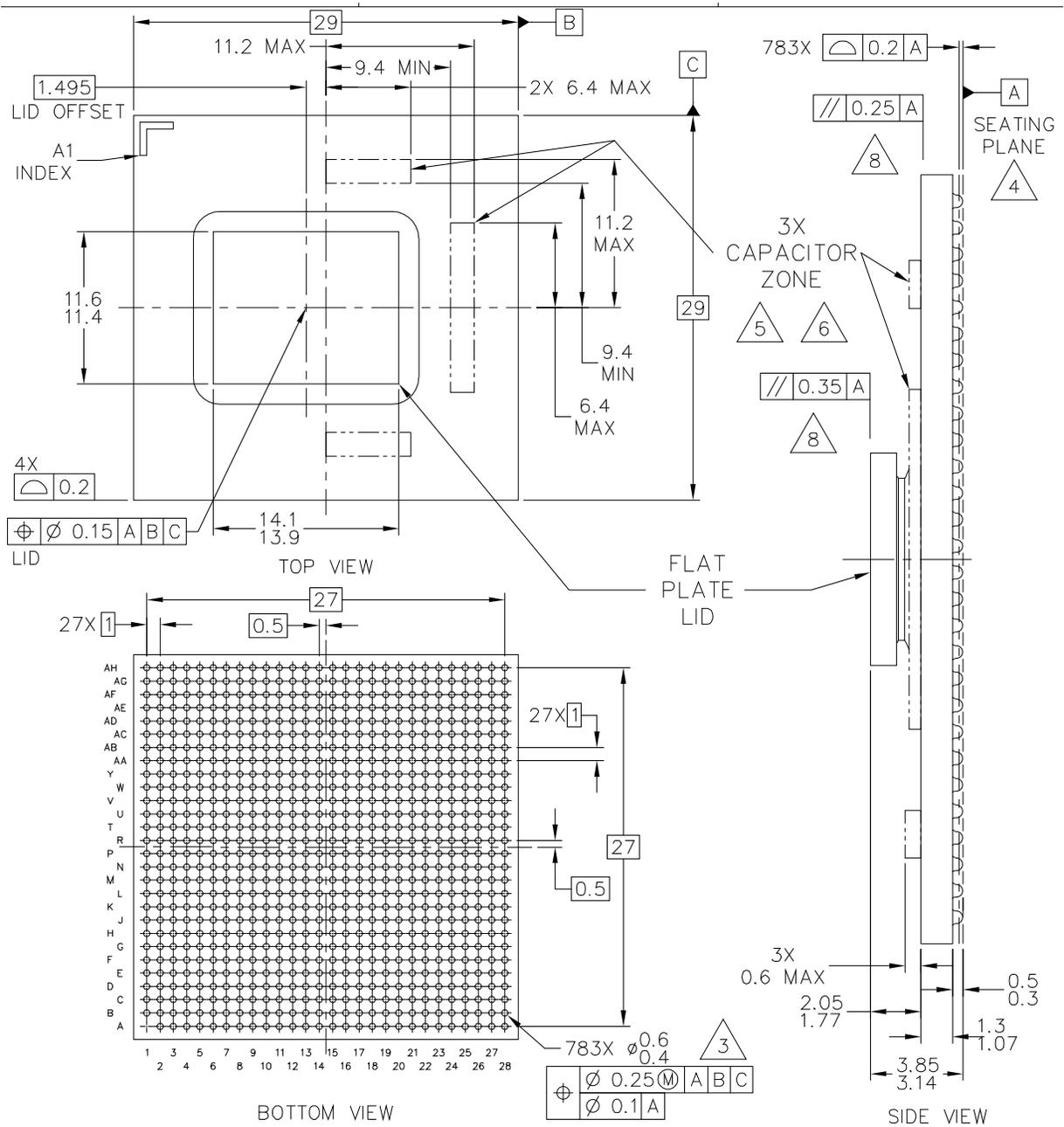


Figure 44. Mechanical Dimensions and Bottom Surface Nomenclature of the MPC8540 FC-PBGA

### NOTES

1. All dimensions are in millimeters.
2. Dimensions and tolerances per ASME Y14.5M-1994.

3. Maximum solder ball diameter measured parallel to datum A.
4. Datum A, the seating plane, is defined by the spherical crowns of the solder balls.
5. Capacitors may not be present on all devices.
6. Caution must be taken not to short capacitors or exposed metal capacitor pads on package top.
7. The socket lid must always be oriented to A1.

## 14.3 Pinout Listings

Table 53 provides the pin-out listing for the MPC8540, 783 FC-PBGA package.

**Table 53. MPC8540 Pinout Listing**

Signal	Package Pin Number	Pin Type	Power Supply	Notes
<b>PCI/PCI-X</b>				
PCI_AD[63:0]	AA14, AB14, AC14, AD14, AE14, AF14, AG14, AH14, V15, W15, Y15, AA15, AB15, AC15, AD15, AG15, AH15, V16, W16, AB16, AC16, AD16, AE16, AF16, V17, W17, Y17, AA17, AB17, AE17, AF17, AF18, AH6, AD7, AE7, AH7, AB8, AC8, AF8, AG8, AD9, AE9, AF9, AG9, AH9, W10, Y10, AA10, AE11, AF11, AG11, AH11, V12, W12, Y12, AB12, AD12, AE12, AG12, AH12, V13, Y13, AB13, AC13	I/O	OV <sub>DD</sub>	17
PCI_C_B $\bar{E}$ [7:0]	AG13, AH13, V14, W14, AH8, AB10, AD11, AC12	I/O	OV <sub>DD</sub>	17
PCI_PAR	AA11	I/O	OV <sub>DD</sub>	
PCI_PAR64	Y14	I/O	OV <sub>DD</sub>	
$\bar{P}CI\_FRAME$	AC10	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_TRDY$	AG10	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_IRDY$	AD10	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_STOP$	V11	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_DEVSEL$	AH10	I/O	OV <sub>DD</sub>	2
PCI_IDSEL	AA9	I	OV <sub>DD</sub>	
$\bar{P}CI\_REQ64$	AE13	I/O	OV <sub>DD</sub>	5, 10
$\bar{P}CI\_ACK64$	AD13	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_PERR$	W11	I/O	OV <sub>DD</sub>	2
$\bar{P}CI\_SERR$	Y11	I/O	OV <sub>DD</sub>	2, 4
$\bar{P}CI\_REQ0$	AF5	I/O	OV <sub>DD</sub>	
$\bar{P}CI\_REQ[1:4]$	AF3, AE4, AG4, AE5	I	OV <sub>DD</sub>	
$\bar{P}CI\_GNT[0]$	AE6	I/O	OV <sub>DD</sub>	
$\bar{P}CI\_GNT[1:4]$	AG5, AH5, AF6, AG6	O	OV <sub>DD</sub>	5, 9

Table 53. MPC8540 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
<b>System Control</b>				
$\overline{\text{HRESET}}$	AH16	I	$\text{OV}_{\text{DD}}$	
$\overline{\text{HRESET\_REQ}}$	AG20	O	$\text{OV}_{\text{DD}}$	
$\overline{\text{SRESET}}$	AF20	I	$\text{OV}_{\text{DD}}$	
$\overline{\text{CKSTP\_IN}}$	M11	I	$\text{OV}_{\text{DD}}$	
$\overline{\text{CKSTP\_OUT}}$	G1	O	$\text{OV}_{\text{DD}}$	2, 4
<b>Debug</b>				
TRIG_IN	N12	I	$\text{OV}_{\text{DD}}$	
TRIG_OUT/READY	G2	O	$\text{OV}_{\text{DD}}$	6, 9, 19
MSRCID[0:1]	J9, G3	O	$\text{OV}_{\text{DD}}$	5, 6, 9
MSRCID[2:4]	F3, F5, F2	O	$\text{OV}_{\text{DD}}$	6
MDVAL	F4	O	$\text{OV}_{\text{DD}}$	6
<b>Clock</b>				
SYSCLK	AH21	I	$\text{OV}_{\text{DD}}$	
RTC	AB23	I	$\text{OV}_{\text{DD}}$	
CLK_OUT	AF22	O	$\text{OV}_{\text{DD}}$	11
<b>JTAG</b>				
TCK	AF21	I	$\text{OV}_{\text{DD}}$	
TDI	AG21	I	$\text{OV}_{\text{DD}}$	12
TDO	AF19	O	$\text{OV}_{\text{DD}}$	11
TMS	AF23	I	$\text{OV}_{\text{DD}}$	12
$\overline{\text{TRST}}$	AG23	I	$\text{OV}_{\text{DD}}$	12
<b>DFT</b>				
$\overline{\text{LSSD\_MODE}}$	AG19	I	$\text{OV}_{\text{DD}}$	21
L1_TSTCLK	AB22	I	$\text{OV}_{\text{DD}}$	21
L2_TSTCLK	AG22	I	$\text{OV}_{\text{DD}}$	21
TEST_SEL	AH20	I	$\text{OV}_{\text{DD}}$	3
<b>Thermal Management</b>				
THERM0	AG2	I	—	14
THERM1	AH3	I	—	14

Table 53. MPC8540 Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
<b>Power Management</b>				
ASLEEP	AG18	I/O		9, 19
<b>Power and Ground Signals</b>				
AV <sub>DD1</sub>	AH19	Power for e500 PLL (1.2 V)	AV <sub>DD1</sub>	
AV <sub>DD2</sub>	AH18	Power for CCB PLL (1.2 V)	AV <sub>DD2</sub>	
GND	A12, A17, B3, B14, B20, B26, B27, C2, C4, C11, C17, C19, C22, C27, D8, E3, E12, E24, F11, F18, F23, G9, G12, G25, H4, H12, H14, H17, H20, H22, H27, J19, J24, K5, K9, K18, K23, K28, L6, L20, L25, M4, M12, M14, M16, M22, M27, N2, N13, N15, N17, P12, P14, P16, P23, R13, R15, R17, R20, R26, T3, T8, T10, T12, T14, T16, U6, U13, U15, U16, U17, U21, V7, V10, V26, W5, W18, W23, Y8, Y16, AA6, AA13, AB4, AB11, AB19, AC6, AC9, AD3, AD8, AD17, AF2, AF4, AF10, AF13, AF15, AF27, AG3, AG7, AG26	—	—	
GV <sub>DD</sub>	A14, A20, A25, A26, A27, A28, B17, B22, B28, C12, C28, D16, D19, D21, D24, D28, E17, E22, F12, F15, F19, F25, G13, G18, G20, G23, G28, H19, H24, J12, J17, J22, J27, K15, K20, K25, L13, L23, L28, M25, N21	Power for DDR DRAM I/O Voltage (2.5 V)	GV <sub>DD</sub>	
LV <sub>DD</sub>	A4, C5, E7, H10	Reference Voltage; Three-Speed Ethernet I/O (2.5 V, 3.3 V)	LV <sub>DD</sub>	
MV <sub>REF</sub>	N27	Reference Voltage Signal; DDR	MV <sub>REF</sub>	
No Connects	AH26, AH27, AH28, AG28, AF28, AE28, AH1, AG1, AH2, B1, B2, A2, A3, AH25, H1, H2, J1, J2, J3, J4, J5, J6, J7, J8, K8, K7, K6, K3, K2, K1, L1, L2, L3, L4, L5, L8, L9, L10, L11, M10, M9, M8, M7, M6, M3, M2, P7, P6, P5, P4, P3, P2, P1, R1, R2, R3, R4, R5, R6, R7, R8, R9, R10, R11, T9, T6, T5, T4, T1, U1, U2, U3, U4, U8, U10, V5, V4, V3, V2, V1, W1, W2, W3, W6, W7, W8, W9, Y1, Y2, Y3, Y4, Y5, Y6, Y9, AA8, AA7, AA4, AA3, AA2, AA1, AB1, AB2, AB3, AB5, AB6, AC7, AC4, AC3, AC2, AC1	—	—	16
OV <sub>DD</sub>	D1, E4, H3, K4, K10, L7, M5, N3, P22, R19, R25, T2, T7, U5, U20, U26, V8, W4, W13, W19, W21, Y7, Y23, AA5, AA12, AA16, AA20, AB7, AB9, AB26, AC5, AC11, AC17, AD4, AE1, AE8, AE10, AE15, AF7, AF12, AG27, AH4	PCI/PCI-X, RapidIO, 10/100 Ethernet, and other Standard (3.3 V)	OV <sub>DD</sub>	

# 15 Clocking

This section describes the PLL configuration of the MPC8540. Note that the platform clock is identical to the CCB clock.

## 15.1 Clock Ranges

Table 54 provides the clocking specifications for the processor core and Table 55 provides the clocking specifications for the memory bus.

**Table 54. Processor Core Clocking Specifications**

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	667 MHz		833 MHz		1 GHz			
	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	400	667	400	833	400	1000	MHz	1, 2, 3

**Notes:**

- 1.) **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to [Section 15.2, "Platform/System PLL Ratio,"](#) and [Section 15.3, "e500 Core PLL Ratio,"](#) for ratio settings.
- 2.) The minimum e500 core frequency is based on the minimum platform frequency of 200 MHz.
- 3.) The 1.0 GHz core frequency is based on a 1.3 V VDD supply voltage.

**Table 55. Memory Bus Clocking Specifications**

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	667 MHz		833 MHz		1 GHz			
	Min	Max	Min	Max	Min	Max		
Memory bus frequency	100	166	100	166	100	166	MHz	1, 2, 3

**Notes:**

- 1.) **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to [Section 15.2, "Platform/System PLL Ratio,"](#) and [Section 15.3, "e500 Core PLL Ratio,"](#) for ratio settings.
- 2.) The memory bus speed is half of the DDR data rate, hence, half of the platform clock frequency.
- 3.) The 1.0 GHz core frequency is based on a 1.3 V VDD supply voltage.

Conductivity	Value	Unit
<b>Lid (12 × 14 × 1 mm)</b>		
$k_x$	360	W/(m × K)
$k_y$	360	
$k_z$	360	
<b>Lid Adhesive—Collapsed resistance (10 × 12 × 0.050 mm)</b>		
$k_x$	1	
$k_y$	1	
$k_z$	1	
<b>Die (10 × 12 × 0.76 mm)</b>		
<b>Bump/Underfill—Collapsed resistance (10 × 12 × 0.070 mm)</b>		
$k_x$	0.6	
$k_y$	0.6	
$k_z$	1.9	
<b>Substrate and Solder Balls (29 × 29 × 1.47 mm)</b>		
$k_x$	10.2	
$k_y$	10.2	
$k_z$	1.6	

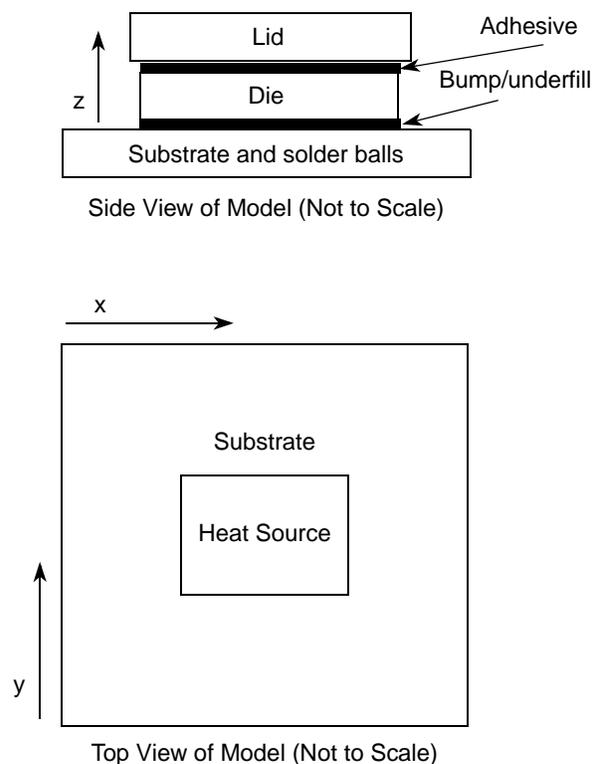


Figure 46. MPC8540 Thermal Model

## 16.2.2 Internal Package Conduction Resistance

For the packaging technology, shown in [Table 59](#), the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

## 17 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8540.

### 17.1 System Clocking

The MPC8540 includes two PLLs.

1. The platform PLL generates the platform clock from the externally supplied SYSCLK input. The frequency ratio between the platform and SYSCLK is selected using the platform PLL ratio configuration bits as described in [Section 15.2, “Platform/System PLL Ratio.”](#)
2. The e500 Core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e500 core clock and the platform clock is selected using the e500 PLL ratio configuration bits as described in [Section 15.3, “e500 Core PLL Ratio.”](#)

### 17.2 PLL Power Supply Filtering

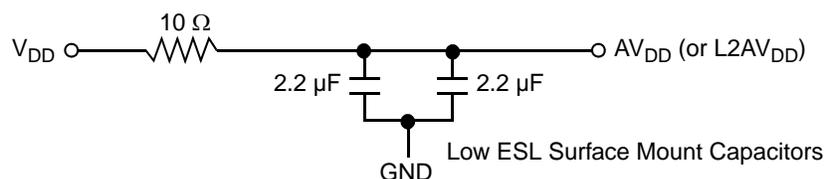
Each of the PLLs listed above is provided with power through independent power supply pins ( $AV_{DD1}$  and  $AV_{DD2}$ , respectively). The  $AV_{DD}$  level should always be equivalent to  $V_{DD}$ , and preferably these voltages will be derived directly from  $V_{DD}$  through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide three independent filter circuits as illustrated in [Figure 52](#), one to each of the three  $AV_{DD}$  pins. By providing independent filters to each PLL the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific  $AV_{DD}$  pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the  $AV_{DD}$  pin, which is on the periphery of the 783 FC-PBGA footprint, without the inductance of vias.

[Figure 52](#) shows the PLL power supply filter circuit.



**Figure 52. PLL Power Supply Filter Circuit**

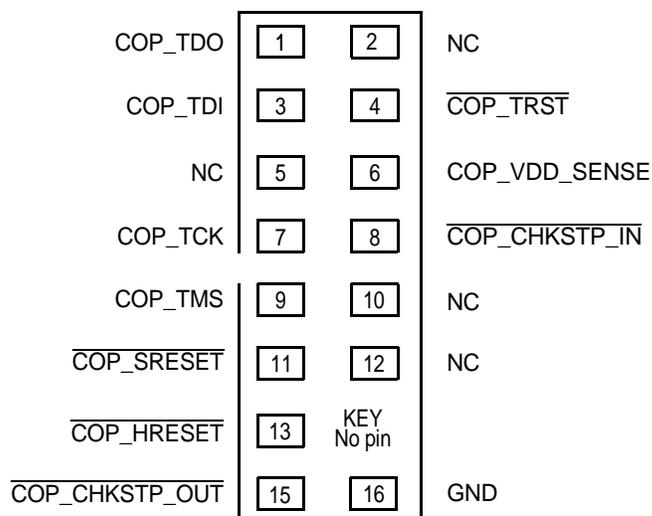


Figure 54. COP Connector Physical Pinout

### 17.8.1 Termination of Unused Signals

If the JTAG interface and COP header will not be used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$  should be tied to  $\overline{\text{HRESET}}$  through a 0 k $\Omega$  isolation resistor so that it is asserted when the system reset signal ( $\overline{\text{HRESET}}$ ) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in Figure 55. If this is not possible, the isolation resistor will allow future access to  $\overline{\text{TRST}}$  in case a JTAG interface may need to be wired onto the system in future debug situations.
- Tie TCK to  $\text{OV}_{\text{DD}}$  through a 10 k $\Omega$  resistor. This will prevent TCK from changing state and reading incorrect data into the device.
- No connection is required for TDI, TMS, or TDO.

Table 61. Document Revision History (continued)

Rev. No.	Substantive Change(s)
2.0	<p>Section 1.1—Updated features list to coincide with latest version of the reference manual</p> <p>Table 1 and Table 2—Addition of SYSCLK to <math>OV_{IN}</math></p> <p>Table 2—Addition of notes 1 and 2</p> <p>Table 3—Addition of note 1</p> <p>Table 5—New</p> <p>Section 4—New</p> <p>Table 13—Addition of <math>I_{VREF}</math></p> <p>Removed Figure 4 DDR SRAM Input Timing Diagram</p> <p>Table 15—Modified maximum values for <math>t_{DISKEW}</math></p> <p>Table 16—Added MSYNC_OUT to <math>t_{MCKSKEW2}</math></p> <p>Figure 5—New</p> <p>Section 6.2.1—Removed Figure 4, “DDR SDRAM Input Timing Diagram”</p> <p>Section 8.1—Removed references to 2.5 V from first paragraph</p> <p>Figure 8—New</p> <p>Table 21 and Table 22—Modified “conditions” for <math>I_{IH}</math> and <math>I_{IL}</math></p> <p>Table 23—Addition of min and max for GTX_CLK125 reference clock duty cycle</p> <p>Table 27 —Addition of min and max for GTX_CLK125 reference clock duty cycle</p> <p>Table 29—Addition of min and max for GTX_CLK125 reference clock duty cycle</p> <p>Table 30—VOH min and conditions; <math>I_{IH}</math> and <math>I_{IL}</math> conditions</p> <p>Table 31—Min and max for <math>t_{MTXR}</math> and <math>t_{MTXF}</math></p> <p>Table 32—Min and max for <math>t_{MRXR}</math> and <math>t_{MRXF}</math></p> <p>Figure 23 and Figure 24—Changed LSYNC_IN to Internal clock at top of each figure</p> <p>Figure 18—New</p> <p>Figure 18—New</p> <p>Table 36—Removed row for <math>t_{LBKHOX3}</math></p> <p>Table 43—New (AC timing of PCI-X at 66 MHz)</p> <p>Table 53—Addition of note 19</p> <p>Figure 55—Addition of jumper and note at top of diagram</p> <p>Table 55: Changed max bus freq for 667 core to 166</p> <p>Section 16.2.1—Modified first paragraph</p> <p>Figure 46—Modified</p> <p>Figure 47—New</p> <p>Table 59—Modified thermal resistance data</p> <p>Section 16.2.4.2—Modified first and second paragraphs</p>